

Abstract

The invention relates to an arrangement having p-doped semiconductor layers (12) and n-doped semiconductor layers (14, 10) which exhibits transitions between the p-doped semiconductor layers (12) and n-doped semiconductor layers (14, 10), the transitions displaying a Zener breakdown upon application of a voltage characteristic of a transition, a plurality of transitions between p-doped semiconductor layers (12) and n-doped semiconductor layers (14, 10) being present, and the characteristic voltages additively make up the breakdown voltage of the entire arrangement. The invention further concerns a method for manufacturing an arrangement according to the present invention.

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